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(57) **ABSTRACT**

An organic light emitting display (OLED) device includes a substrate having a display region and a peripheral region at least partially surrounding the display region. An insulating layer structure is disposed on the substrate within both the display region and the peripheral region. The insulating layer structure includes a groove in the peripheral region. A plurality of pixel structures is disposed in the display region on the insulating layer structure. A block structure is disposed in the peripheral region so as to at least partially overlap the groove of the insulating layer structure. The block structure at least partially fills the groove of the insulating layer structure.

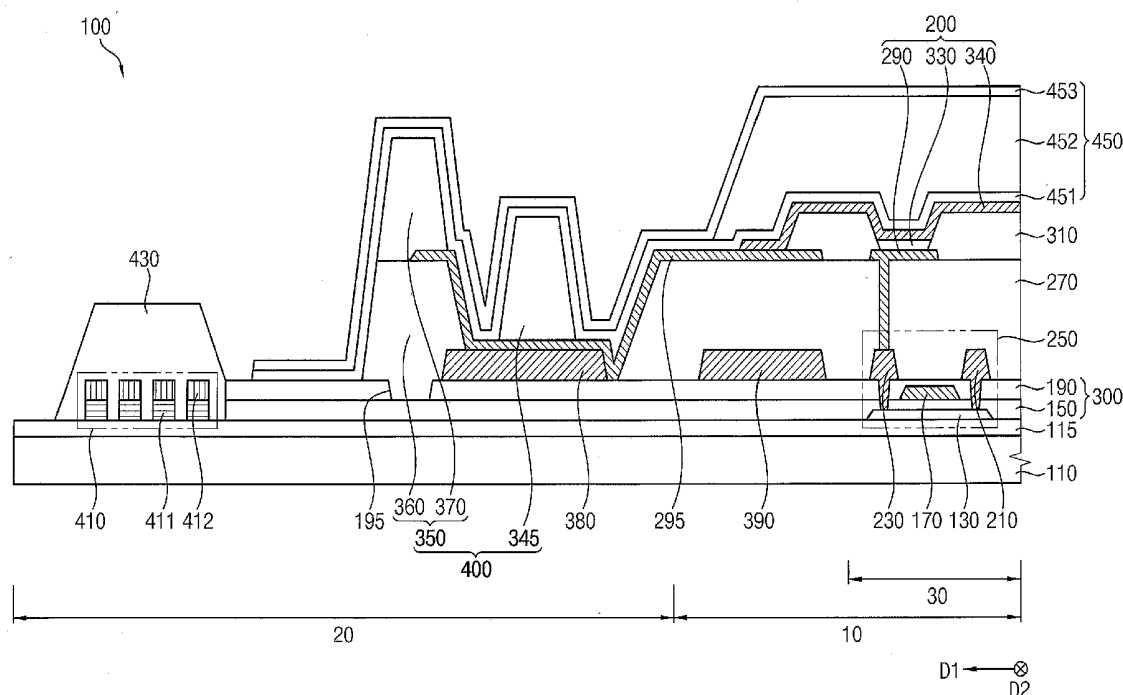
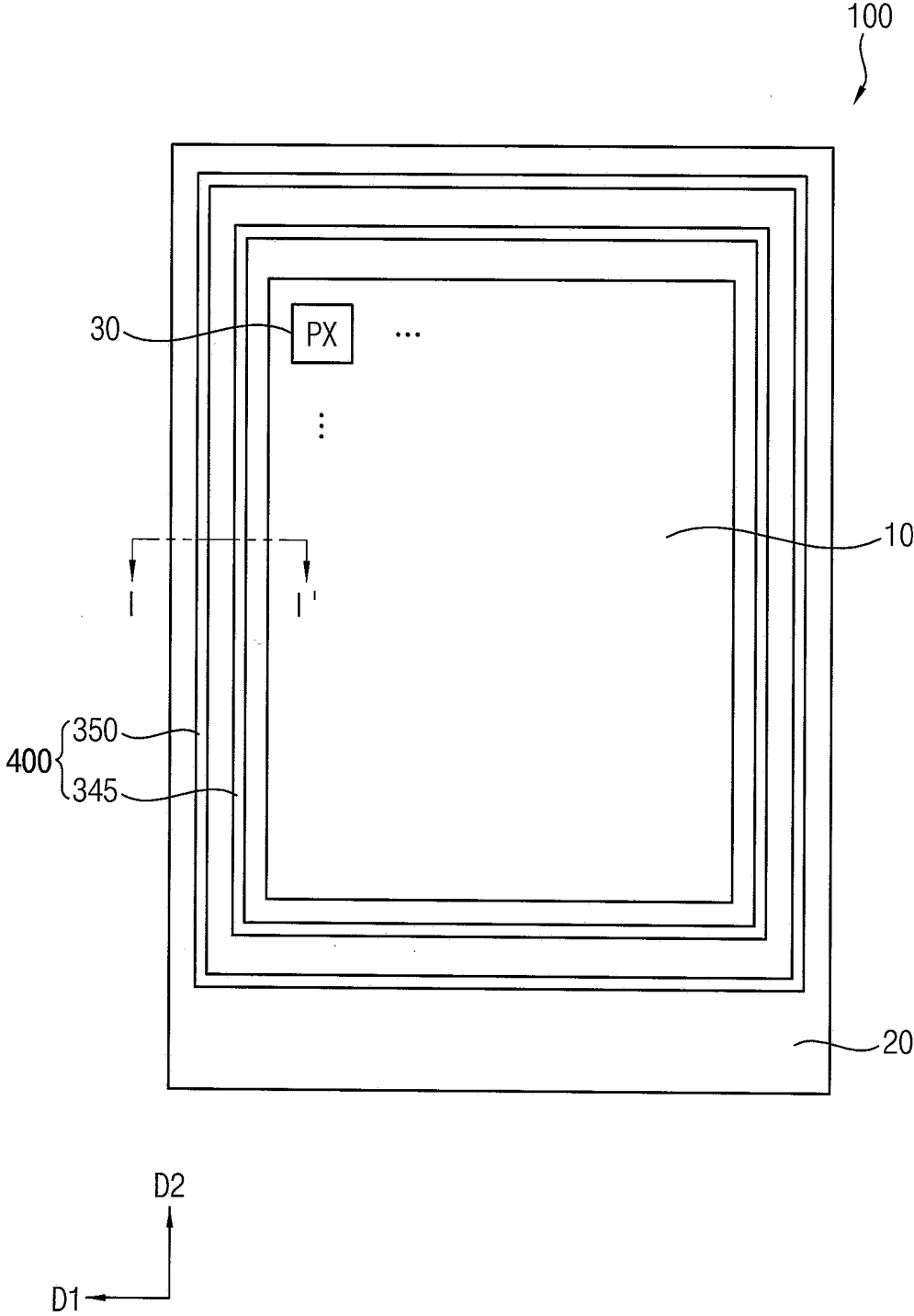


FIG. 1



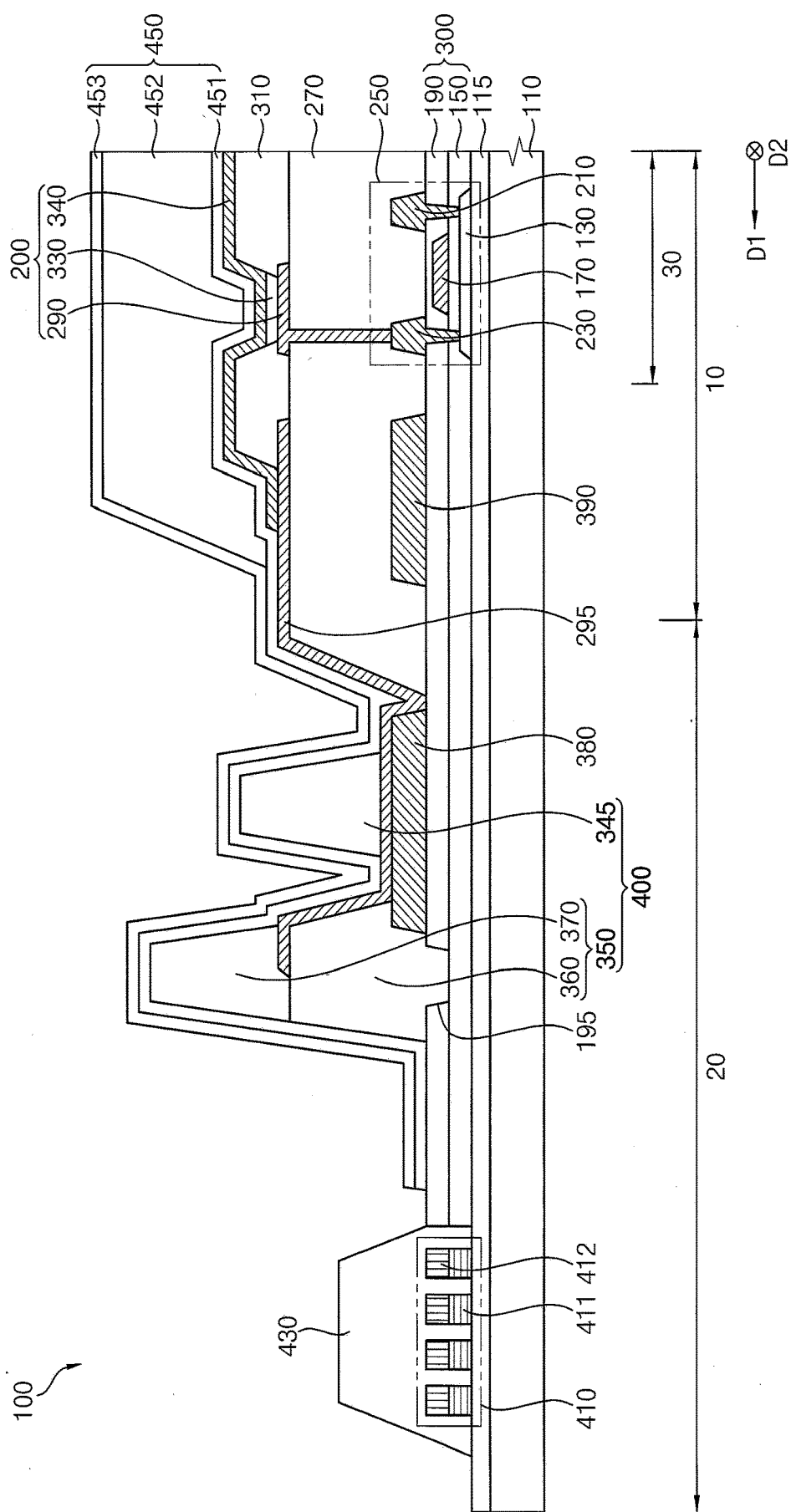


FIG. 3

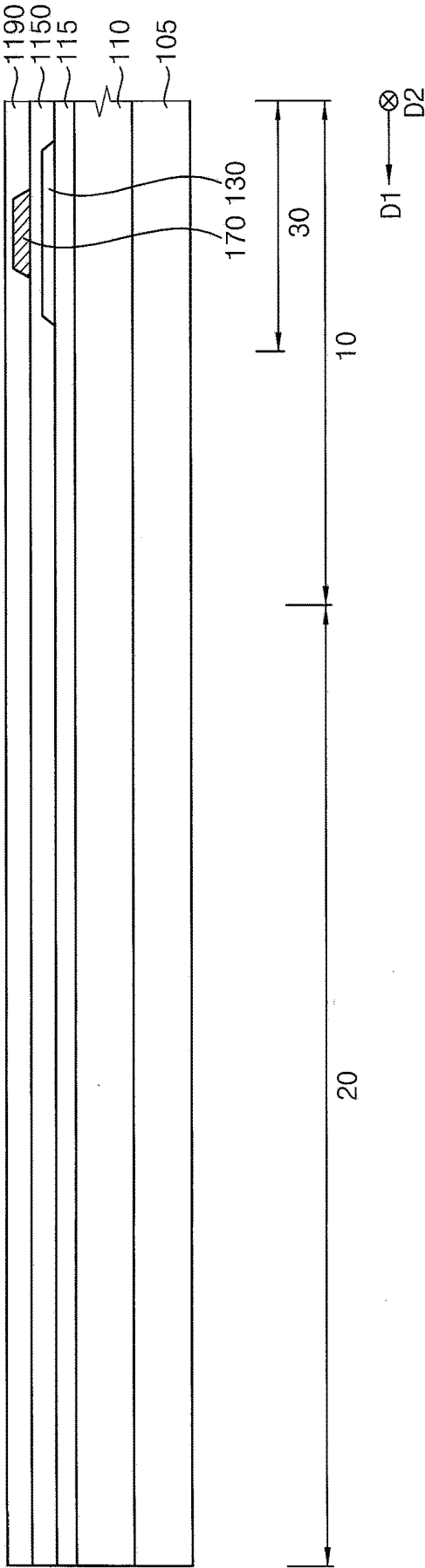


FIG. 4

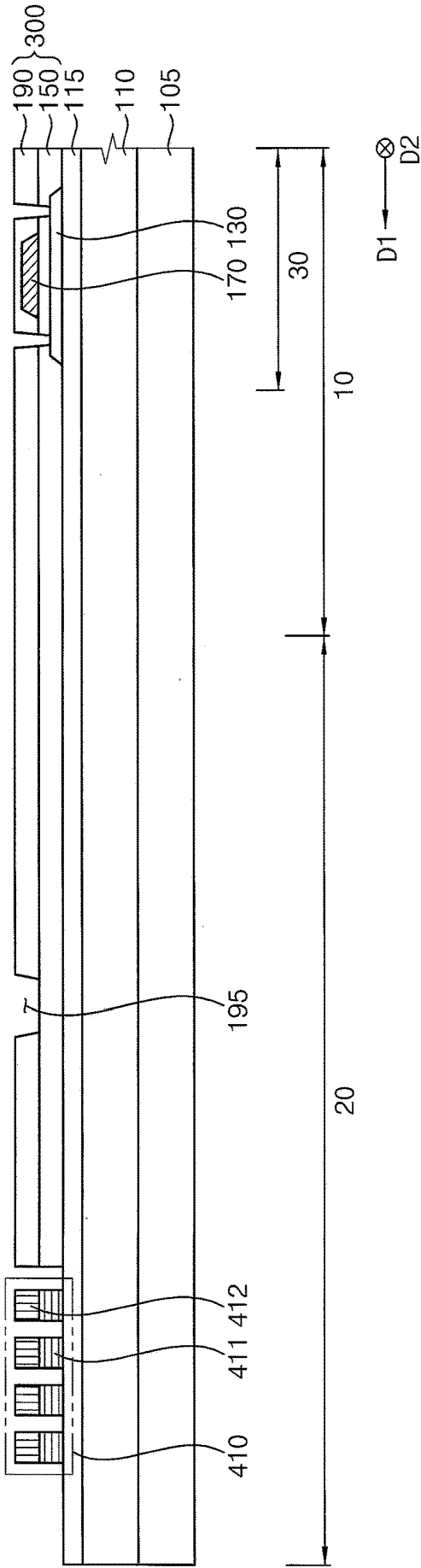


FIG. 7

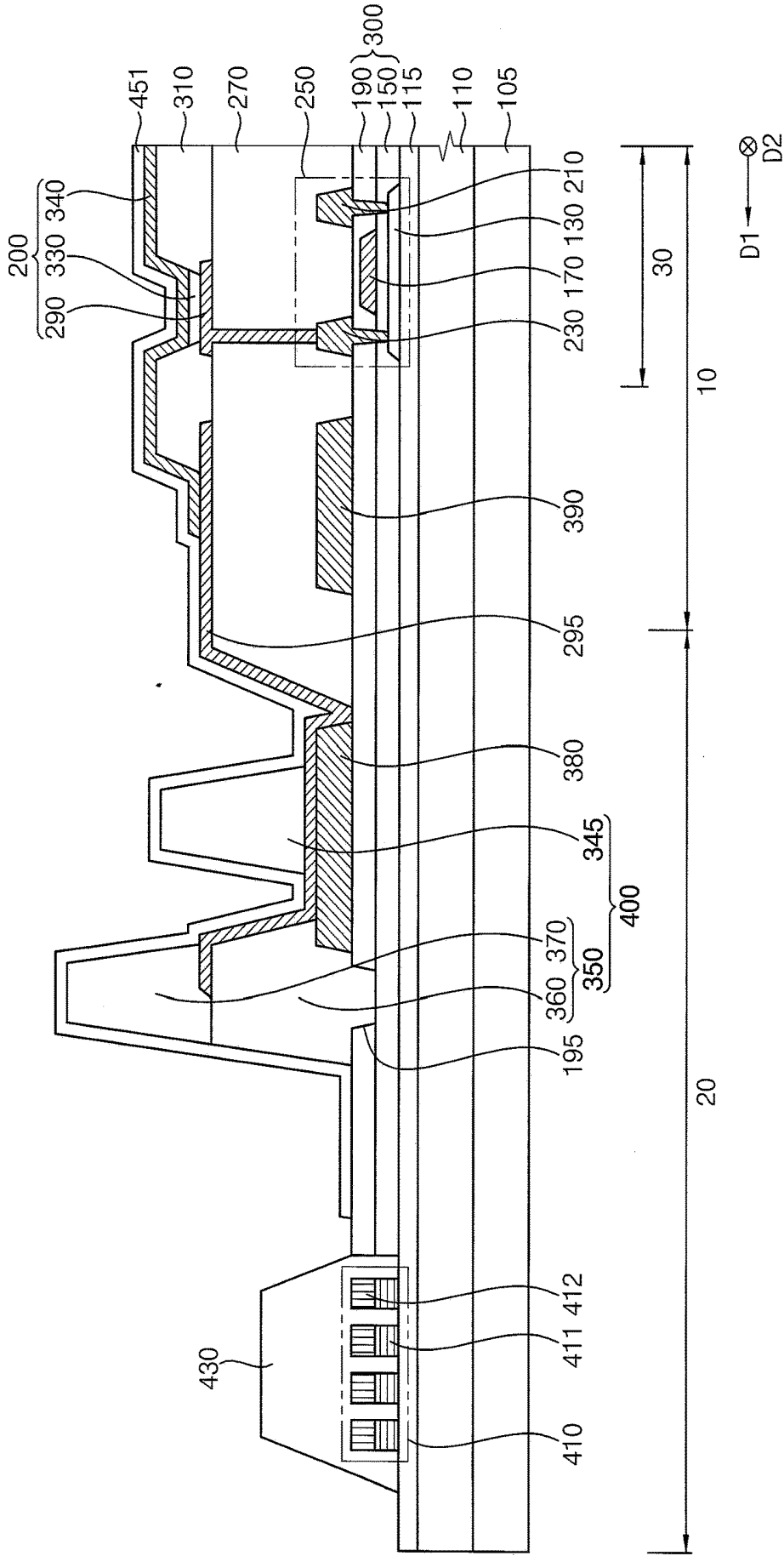
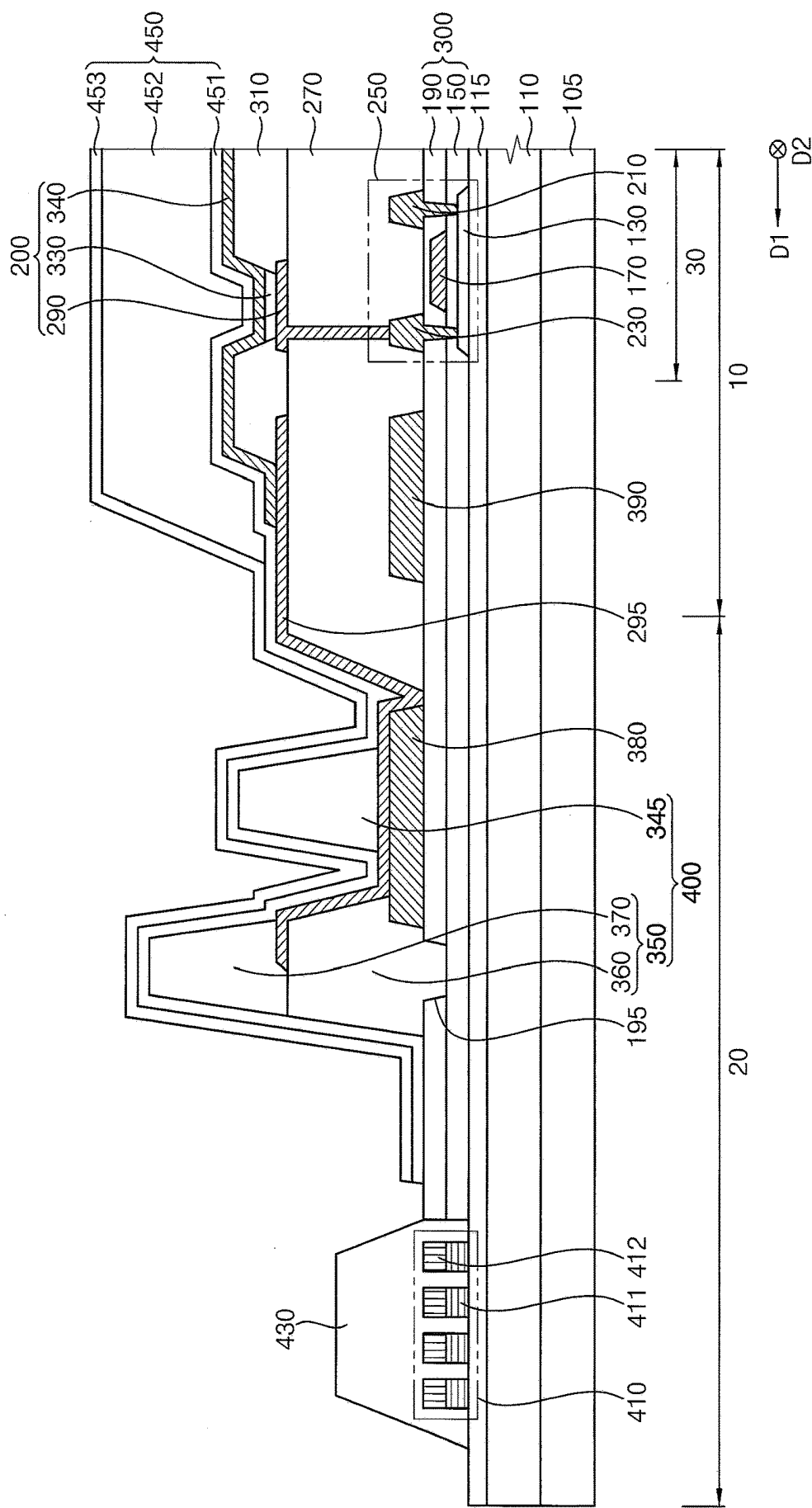


FIG. 8



FLEXIBLE ORGANIC LIGHT EMITTING DISPLAY DEVICE

CROSS-REFERENCE TO RELATED APPLICATION(S)

[0001] This application claims priority under 35 USC § 119 to Korean Patent Applications No. 10-2018-0003923, filed on Jan. 11, 2018 in the Korean Intellectual Property Office (KIPO), the contents of which are incorporated by reference herein in its entirety.

TECHNICAL FIELD

[0002] The present disclosure relates to a display device and, more particularly, to a flexible organic light emitting display device.

DISCUSSION OF THE RELATED ART

[0003] A flat panel display (FPD) device is widely used on account of its light weight and thin profile as compared to conventional display devices such as cathode-ray tube (CRT) display devices. Typical examples of FPD devices include a liquid crystal display (LCD) device and an organic light emitting display (OLED) device.

[0004] Recently, flexible OLED devices capable of being bent or folded have been developed. These flexible OLED devices may include lower and upper substrates made of flexible materials. For example, the lower substrate may include a flexible substrate, and the upper substrate may have a thin film encapsulation (TFE) structure. Here, the TFE structure may include an inorganic layer and an organic layer that are alternately stacked. A block structure may be disposed beyond (e.g., outside of) the flexible OLED device so as to prevent (or block) a reflow (or leakage) of the organic layer. Meanwhile, as a dead space (e.g., a peripheral region) of the flexible OLED device becomes slimmer (or smaller), a size (e.g., a width) of elements (e.g., the block structure) disposed in the dead space may be reduced. In this case, since a contact surface is reduced in a lower surface of the block structure having a relatively reduced width, a contact failure of the block structure may occur, and thus a defect of the flexible OLED device may occur.

SUMMARY

[0005] An organic light emitting display (OLED) device includes a substrate having a display region and a peripheral region at least partially surrounding the display region. An insulating layer structure is disposed on the substrate within both the display region and the peripheral region. The insulating layer structure includes a groove in the peripheral region. A plurality of pixel structures is disposed in the display region on the insulating layer structure. A block structure is disposed in the peripheral region so as to at least partially overlap the groove of the insulating layer structure. The block structure at least partially fills the groove of the insulating layer structure.

[0006] An OLED device includes a substrate having a display region including a plurality of pixel regions and a peripheral region at least partially surrounding the display region. An insulating layer structure is disposed on the substrate. The insulating layer structure has an opening in the peripheral region. A plurality of pixel structures is disposed in the pixel region on the insulating layer structure. A block structure is disposed in the peripheral region to at

least partially overlap the opening of the insulating layer structure. The block structure at least partially fills the opening of the insulating layer structure. A shock absorbing structure is disposed in the peripheral region on the substrate. The shock absorbing structure is spaced apart from the block structure, the shock absorbing structure having a plurality of concave and convex patterns.

[0007] An OLED device includes a substrate having a display region including a plurality of pixel regions and a peripheral region at least partially surrounding the display region. An insulating layer structure is disposed on the substrate. The insulating layer structure has a plurality of grooves disposed in the peripheral region. A plurality of pixel structures is disposed in the pixel region on the insulating layer structure. A block structure is disposed in the peripheral region to at least partially overlap the grooves of the insulating layer structure. The block structure at least partially fills the grooves of the insulating layer structure. A shock absorbing structure is disposed in the peripheral region on the substrate. The shock absorbing structure is spaced apart from the block structure. The shock absorbing structure has a plurality of concave and convex patterns.

BRIEF DESCRIPTION OF THE DRAWINGS

[0008] A more complete appreciation of the present disclosure and many of the attendant aspects thereof will be readily obtained as the same becomes better understood by reference to the following detailed description taken in conjunction with the accompanying drawings, in which:

[0009] FIG. 1 is a plan view illustrating an organic light emitting display (OLED) device in accordance with exemplary embodiments of the present disclosure;

[0010] FIG. 2 is a cross-sectional view taken along a line I-I' of FIG. 1;

[0011] FIGS. 3 through 8 are cross-sectional views illustrating a method of manufacturing an OLED device in accordance with exemplary embodiments of the present disclosure;

[0012] FIG. 9 is a cross-sectional view illustrating an OLED device in accordance with exemplary embodiments of the present disclosure;

[0013] FIG. 10 is a cross-sectional view illustrating an OLED device in accordance with exemplary embodiments of the present disclosure; and

[0014] FIG. 11 is a cross-sectional view illustrating an OLED device in accordance with exemplary embodiments of the present disclosure.

DETAILED DESCRIPTION OF THE EMBODIMENTS

[0015] Hereinafter, embodiments of the present inventive concept will be explained in detail with reference to the accompanying drawings. In describing exemplary embodiments of the present disclosure, specific terminology is employed for sake of clarity. However, the present disclosure is not intended to be limited to the specific terminology so selected, and it is to be understood that each specific element includes all technical equivalents which operate in a similar manner.

[0016] FIG. 1 is a plan view illustrating an organic light emitting display (OLED) device in accordance with exemplary embodiments of the present disclosure, and FIG. 2 is a cross-sectional view taken along a line I-I' of FIG. 1.

[0017] Referring to FIGS. 1 and 2, an organic light emitting display (OLED) device 100 may have a display region 10 and a peripheral region 20. Here, the display region 10 may include a plurality of pixel regions 30.

[0018] Pixel structures PX (e.g., a pixel structure 200 of FIG. 2) may be disposed in the display region 10. A display image may be displayed in the display region 10 through the pixel structure PX. Wirings (e.g., scan wirings, data wirings, power supply voltage wirings, etc.) and a block structure 400 may be disposed in the peripheral region 20. Here, the wirings may be electrically connected to the pixel structure PX, and the block structure 400 may include a first block pattern 345 and a second block pattern 350.

[0019] According to exemplary embodiments of the present disclosure, the first block pattern 345 may be disposed in the peripheral region 20 that is adjacent to a boundary of the display region 10 and the peripheral region 20, and the first block pattern 345 may at least partially surround the pixel structures PX. The second block pattern 350 may at least partially surround the first block pattern 345. A height of the second block pattern 350 may be greater than a height of the first block pattern 345. For example, the first block pattern 345 might not be in contact with the second block pattern 350, and they may be parallel to each other. The block structure 400 may prevent a leakage of a second thin film encapsulation (TFE) layer included in a TFE structure. In addition, as the OLED device 100 includes a flexible substrate and the TFE structure, the OLED device 100 may serve as a flexible OLED device.

[0020] A shape of each of the display and peripheral regions 10 and 20 illustrated in FIG. 1 may have a plan shape that is substantially square (or substantially rectangular), but other shapes may be used. For example, each of the display and peripheral regions 10 and 20 may be substantially triangular, substantially diamond shaped, substantially polygonal, substantially circular, substantially stadium shaped or oval shaped, or substantially elliptical.

[0021] FIG. 2 is a cross-sectional view taken along a line I-I' of FIG. 1.

[0022] Referring to FIG. 2, an OLED device 100 may include a substrate 110, a buffer layer 115, a semiconductor element 250, an insulating layer structure 300, a shock absorbing structure 410, a first power supply voltage wiring 380, a second power supply voltage wiring 390, a planarization layer 270, a protective insulation layer 430, a block structure 400, a pixel structure 200, a connection pattern 295, a pixel defining layer 310, a TFE structure 450, etc. Here, the pixel structure 200 may include a lower electrode 290, a light emitting layer 330, and an upper electrode 340. The semiconductor element 250 may include an active layer 130, a gate electrode 170, a source electrode 210, and a drain electrode 230. In addition, the TFE structure 450 may include a first TFE layer 451, a second TFE layer 452, and a third TFE layer 453. The shock absorbing structure 410 may include a first set of concave and convex patterns 411 and a second set of concave and convex patterns 412. Further, the insulating layer structure 300 may include a gate insulation layer 150 and an insulating interlayer 190. The block structure 400 may include a first block pattern 345 and a second block pattern 350. Here, the second block pattern 350 may include a first sub-block pattern 360 and a second sub-block pattern 370.

[0023] As described above, the OLED device 100 may include a display region 10 including a plurality of pixel

regions 30 and a peripheral region 20 surrounding the display region 10. A display image may be displayed in the display region 10 through the pixel structure 200. The block structure 400, the shock absorbing structure 410, wirings, etc. may be disposed in the peripheral region 20 (e.g., non-display region). A plurality of transistors, a plurality of capacitors, a plurality of wirings, etc. may be further disposed in the display region 10. As the OLED device 100 includes a flexible substrate 110 and the TFE structure 450, the OLED device 100 may serve as a flexible OLED device.

[0024] The substrate 110 having opaque or transparent materials may be provided. The substrate 110 may include a flexible transparent resin substrate. According to some exemplary embodiments of the present disclosure, the substrate 110 may have a configuration where a first organic layer, a first barrier layer, a second organic layer, and a second barrier layer are sequentially stacked. The first barrier layer and the second barrier layer may each include inorganic materials such as silicon oxide, etc. In addition, the first organic layer and the second organic layer may each include organic materials such as a polyamide-based resin. According to exemplary embodiments of the present disclosure, each of the first and second barrier layers may block moisture or water that may permeate through the first and second organic layers.

[0025] Since the substrate 110 is relatively thin and flexible, the substrate 110 may be disposed on a rigid glass substrate, during fabrication, to help support the formation of the semiconductor element 250 and the pixel structure 200. In a manufacturing the OLED device 100, after the buffer layer 115 is disposed on the second barrier layer of the substrate 110, the semiconductor element 250 and the pixel structure 200 may be disposed on the buffer layer 115. After the semiconductor element 250 and the pixel structure 200 are formed on the insulation layer, the rigid glass substrate on which the substrate 110 is disposed may be removed. It may be difficult to directly form the semiconductor element 250 and the pixel structure 200 on the substrate 110 because of the thinness and flexibility of the substrate 110. Accordingly, the semiconductor element 250 and the pixel structure 200 are formed on the substrate 110 and the rigid glass substrate, and then the substrate 110 including the first organic layer, the first barrier layer, the second organic layer, and the second barrier layer may serve as the substrate 110 of the OLED device 100 after the removal of the rigid glass substrate. Alternatively, the substrate 110 may include a quartz substrate, a synthetic quartz substrate, a calcium fluoride substrate, a fluoride-doped quartz substrate, a soda-lime glass substrate, a non-alkali glass substrate etc.

[0026] According to exemplary embodiments of the present disclosure, the substrate 110 includes four-layers, but another number of layers may alternatively be used. For example, in some exemplary embodiments of the present disclosure, the substrate 110 may include a single layer or a plurality of layers.

[0027] As the OLED device 100 may have the pixel region 30 and the peripheral region 20 and the substrate 110 may be divided into the pixel region 30 and the peripheral region 20.

[0028] The buffer layer 115 may be disposed on the substrate 110. The buffer layer 115 may cover the entire substrate 110. The buffer layer 115 may prevent the diffusion of metal atoms and/or impurities from the substrate 110 into the semiconductor element 250 and the pixel structure 200. In addition, the buffer layer 115 may control a rate of a heat

transfer in a crystallization process for forming the active layer **130**, thereby leading to the production of a substantially uniform active layer. Further, the buffer layer **115** may increase a surface flatness of the substrate **110** when a surface of the substrate **110** is relatively irregular. According to a type of the substrate **110**, at least two buffer layers **115** may be disposed on the substrate **110**, or the buffer layer **115** may be omitted. For example, the buffer layer **115** may include organic materials or inorganic materials. In exemplary embodiments of the present disclosure, the buffer layer **115** may include the organic materials.

[0029] The active layer **130** may be disposed in the pixel region **30** on the substrate **110**. The active layer **130** may include an oxide semiconductor, an inorganic semiconductor (e.g., amorphous silicon, polysilicon, etc.), an organic semiconductor, etc.

[0030] The gate insulation layer **150** may be disposed on the buffer layer **115** and the active layer **130**. The gate insulation layer **150** may at least partially cover the active layer **130** in the display region **10** on the buffer layer **115**, and may extend into the peripheral region **20** along a first direction D1 (e.g., a direction from the display region **10** into the peripheral region **20** of FIG. 2). In exemplary embodiments of the present disclosure, the gate insulation layer **150** might not be disposed at the outermost portion of the OLED device **100**. For example, the gate insulation layer **150** may expose an upper surface of the buffer layer **115** that is located at the outermost portion of the OLED device **100**, and a distal end portion of the gate insulation layer **150** that is located in the peripheral region **20** may be spaced apart from the shock absorbing structure **410**. The gate insulation layer **150** may at least partially cover the active layer **130** on the buffer layer **115**, and may have a substantially flat upper surface without a step around the active layer **130**. Alternatively, the gate insulation layer **150** may at least partially cover the active layer **130** on the buffer layer **115**, and may be disposed with a substantially uniform thickness along a profile of the active layer **130**. The gate insulation layer **150** may include a silicon compound, metal oxide, etc.

[0031] The gate electrode **170** may be disposed in the pixel region **30** on the gate insulation layer **150**. For example, the gate electrode **170** may be disposed on a portion of the gate insulation layer **150** under which the active layer **130** is located. The gate electrode **170** may include a metal, a metal alloy, metal nitride, conductive metal oxide, transparent conductive materials, etc. For example, the gate electrode **170** may be formed of gold (Au), an alloy of Au, silver (Ag), an alloy of Ag, aluminum (Al), an alloy of Al, platinum (Pt), an alloy of Pt, nickel (Ni), titanium (Ti), palladium (Pd), magnesium (Mg), calcium (Ca), Lithium (Li), chromium (Cr), an alloy of Cr, tantalum (Ta), tungsten (W), copper (Cu), an alloy of Cu, molybdenum (Mo), an alloy of Mo, scandium (Sc), neodymium (Nd), iridium (Ir), aluminum nitride (AlN_x), titanium nitride (TiN_x), chromium nitride (CrN_x), tantalum nitride (TaN_x), tungsten nitride (WN_x), strontium ruthenium oxide (SRO), zinc oxide (ZnO_x), stannum oxide (SnO_x), indium oxide (InO_x), gallium oxide (GaO_x), indium tin oxide (ITO), indium zinc oxide (IZO), etc. These may be used alone or in a suitable combination thereof. Alternatively, the gate electrode **170** may have a multi-layered structure including a plurality of layers.

[0032] The insulating interlayer **190** may be disposed on the gate insulation layer **150** and the gate electrode **170**. The

insulating interlayer **190** may at least partially cover the gate electrode **170** in the display region **10** on the gate insulation layer **150**, and may extend into the peripheral region **20** along the first direction D1. In exemplary embodiments of the present disclosure, the insulating interlayer **190** may have an opening **195** exposing an upper surface of the gate insulation layer **150** in the peripheral region **20**. For example, the opening **195** may correspond to a groove of the insulating layer structure **300**. The opening **195** may at least partially overlap the second block pattern **350**. In addition, the insulating interlayer **190** might not be disposed at the outermost portion of the OLED device **100**. For example, the insulating interlayer **190** may expose the upper surface of the buffer layer **115** that is located at the outermost portion of the OLED device **100**, and a distal end portion of the insulating interlayer **190** that is located in the peripheral region **20** may be spaced apart from the shock absorbing structure **410**. The insulating interlayer **190** may at least partially cover the gate electrode **170** on the gate insulation layer **150**, and may have a substantially flat upper surface without a step around the gate electrode **170**. Alternatively, the insulating interlayer **190** may at least partially cover the gate electrode **170** on the gate insulation layer **150**, and may be disposed with a substantially uniform thickness along a profile of the gate electrode **170**. The insulating interlayer **190** may include silicon compound, metal oxide, etc. Accordingly, the insulating layer structure **300** including the gate insulation layer **150** and the insulating interlayer **190** may be fabricated. In some exemplary embodiments of the present disclosure, the insulating interlayer **190** may have a groove where at least a portion of the insulating interlayer **190** is removed in the peripheral region **20**. For example, the groove may at least partially overlap the second block pattern **350**, and the first sub-block pattern **360** of the second block pattern **350** may at least partially fill the groove.

[0033] The shock absorbing structure **410** may be disposed in the peripheral region **20** on the buffer layer **115**. In exemplary embodiments of the present disclosure, the shock absorbing structure **410** may be located at the outermost portion of the OLED device **100**, and may be spaced apart from the insulating layer structure **300** in the first direction D1. In addition, the shock absorbing structure **410** and the insulating layer structure **300** may be located within the same layer, and the shock absorbing structure **410** may have a plurality of concave and convex patterns. For example, the shock absorbing structure **410** may include first concave and convex patterns **411** and second concave and convex patterns **412**. The first concave and convex patterns **411** may be disposed on the buffer layer **115**, and may be spaced apart from each other. The second concave and convex patterns **412** may be disposed on the first concave and convex patterns **411**, and may at least partially overlap the first concave and convex patterns **411**. Here, the first concave and convex patterns **411** and the gate insulation layer **150** may be located within the same layer, and may be simultaneously (or concurrently) formed from substantially the same materials. The second concave and convex patterns **412** and the insulating interlayer **190** may be located within the same layer, and may be simultaneously formed from substantially the same materials. The shock absorbing structure **410** may include silicon compound, metal oxide, etc. For example, the shock absorbing structure **410** may be formed of silicon oxide (SiO_x), silicon nitride (SiN_x), silicon oxynitride (SiO_xN_y), silicon oxycarbide (SiO_xC_y), silicon carbon nitride

(SiC_xN_y), aluminum oxide (AlO_x), aluminum nitride (AlN_x), tantalum oxide (TaO_x), hafnium oxide (HfO_x), zirconium oxide (ZrO_x), titanium oxide (TiO_x), etc.

[0034] For example, when an external impact occurs in the outermost portion of the OLED device 100, the amount of the external impact capable of being transmitted to the insulating layer structure 300 may be reduced by the shock absorbing structure 410 because the shock absorbing structure 410 includes the plurality of concave and convex patterns that are spaced apart from each other and because the shock absorbing structure 410 is spaced apart from the insulating layer structure 300. For example, the shock absorbing structure 410 may absorb a portion of the external impact. Accordingly, as the OLED device 100 includes the shock absorbing structure 410, the OLED device 100 may protect the semiconductor element 250, the pixel structure 200, and the TFE structure 450, etc. from the external impact.

[0035] The source electrode 210 and the drain electrode 230 may be disposed in the pixel region 30 on the insulating interlayer 190. The source electrode 210 may be in contact with a first side (e.g., a source region) of the active layer 130 via a contact hole formed by removing a first portion of the gate insulation layer 150 and the insulating interlayer 190. The drain electrode 230 may be in contact with a second side (e.g., a drain region) of the active layer 130 via a contact hole formed by removing a second portion of the gate insulation layer 150 and the insulating interlayer 190. Each of the source electrode 210 and the drain electrode 230 may include a metal, an alloy, metal nitride, conductive metal oxide, transparent conductive materials, etc. These may be used alone or in a suitable combination thereof. Alternatively, each of the source electrode 210 and the drain electrode 230 may have a multi-layered structure including a plurality of layers. Accordingly, the semiconductor element 250 including the active layer 130, the gate electrode 170, the source electrode 210, and the drain electrode 230 may be fabricated.

[0036] In exemplary embodiments of the present disclosure, the OLED device 100 includes one transistor (e.g., the semiconductor element 250), but additional transistors may also be included. For example, in some exemplary embodiments of the present disclosure, the OLED device 100 may include at least two transistors and at least one capacitor.

[0037] In addition, a configuration of the semiconductor element 250 includes the active layer 130, the gate electrode 170, the source electrode 210, and the drain electrode 230, but other configurations may be used. For example, the semiconductor element 250 may have a configuration including the active layer 130, the gate insulation layer 150, the gate electrode 170, the insulating interlayer 190, the source electrode 210, and the drain electrode 230.

[0038] Further, in exemplary embodiments of the present disclosure, the semiconductor element 250 has a top gate structure, but other structures may be used. For example, in some exemplary embodiments of the present disclosure, the semiconductor element 250 may have a bottom gate structure and/or a double gate structure.

[0039] The first power supply voltage wiring 380 may be disposed in the peripheral region 20 on the insulating layer structure 300. In exemplary embodiments of the present disclosure, the first power supply voltage wiring 380 may be located adjacent to a boundary of the display region 10 and the peripheral region 20, and may extend in a second

direction D2 that is perpendicular to the first direction D1. In addition, the first power supply voltage wiring 380 might not overlap the opening 195 of the insulating interlayer 190, and a low power supply voltage may be provided in the first power supply voltage wiring 380. Here, the low power supply voltage may be applied to the upper electrode 340. For example, the first power supply voltage wiring 380 may include a metal, an alloy of a metal, metal nitride, conductive metal oxide, transparent conductive materials, etc. These may be used alone or in a suitable combination thereof. Alternatively, the first power supply voltage wiring 380 may have a multi-layered structure including a plurality of layers.

[0040] The second power supply voltage wiring 390 may be disposed in the display region 10 on the insulating layer structure 300. In exemplary embodiments of the present disclosure, the second power supply voltage wiring 390 may be located adjacent to a boundary of the display region 10 and the peripheral region 20, and may be disposed between the first power supply voltage wiring 380 and the drain electrode 230 on the insulating layer structure 300. In addition, the second power supply voltage wiring 390 may extend in the second direction D2, and a high power supply voltage, which has a higher voltage level than the low power supply voltage, may be provided in the second power supply voltage wiring 390. Here, the high power supply voltage may be applied to the lower electrode 290. For example, the second power supply voltage wiring 390 may include a metal, an alloy of a metal, metal nitride, conductive metal oxide, transparent conductive materials, etc. These may be used alone or in a suitable combination thereof. Alternatively, the second power supply voltage wiring 390 may have a multi-layered structure including a plurality of layers.

[0041] In exemplary embodiments of the present disclosure, the first power supply voltage wiring 380, the second power supply voltage wiring 390, the source electrode 210, and the drain electrode 230 may be located within the same layer, and may be simultaneously formed from substantially the same materials. In some exemplary embodiments of the present disclosure, the OLED device 100 may further include a plurality of wiring patterns in the display region 10. For example, the wiring patterns may be disposed between the first power supply voltage wiring 380 and the drain electrode 230.

[0042] The planarization layer 270 may be disposed on the insulating layer structure 300, the second power supply voltage wiring 390, the source electrode 210, and the drain electrode 230, and might not overlap the first power supply voltage wiring 380. The planarization layer 270 may be disposed as a high thickness to at least partially cover the second power supply voltage wiring 390 and the source and drain electrodes 210 and 230 on the insulating interlayer 190. In this case, the planarization layer 270 may have a substantially flat upper surface, and a planarization process may be further performed on the planarization layer 270 to implement the flat upper surface of the planarization layer 270. In addition, the planarization layer 270 may have a contact hole exposing an upper surface of the drain electrode 230. The planarization layer 270 may include organic materials or inorganic materials. In exemplary embodiments of the present disclosure, the planarization layer 270 may include organic materials.

[0043] The first sub-block pattern 360 may be disposed in the peripheral region 20 on the insulating layer structure

300. In exemplary embodiments of the present disclosure, the first sub-block pattern **360** may at least partially fill the opening **195** of the insulating interlayer **190**, and may be in direct contact with an upper surface of the gate insulation layer **150**. The first sub-block pattern **360** may at least partially overlap a portion of the first power supply voltage wiring **380**. In addition, the first sub-block pattern **360** may block a leakage of the second TFE layer **452**, and the first sub-block pattern **360** and the planarization layer **270** may be located within the same layer. The first sub-block pattern **360** may include organic materials or inorganic materials. In exemplary embodiments of the present disclosure, the first sub-block pattern **360** may include the organic materials such as polyimide, epoxy-based resin, acryl-based resin, polyester, photoresist, polyacryl-based resin, polyimide-based resin, a polyamide-based resin, a siloxane-based resin, etc.

[0044] For example, as an OLED device becomes slimmer, a width of the peripheral region of the OLED device may be reduced. Thus, a width of each of a shock absorbing structure, a block structure, a first power supply voltage wiring, etc. that are located in the peripheral region **20** may be also reduced. Here, as a width of a second block pattern is reduced, a contact area where an upper surface of an insulating interlayer of the insulating layer structure is in contact with a lower surface of the second block pattern may be reduced. In this case, the second block pattern may be separated from the insulating interlayer due to a relatively low adhesive strength between the second block pattern and the insulating interlayer, and a defect of the OLED device may occur.

[0045] In exemplary embodiments of the present disclosure, as the insulating interlayer **190** includes the opening **195** of the insulating interlayer **190** (e.g., a groove of the insulating interlayer **190**), a contact area of the second block pattern **350** may be relatively increased by the opening **195**. Accordingly, although a width of the second block pattern **350** is relatively reduced, a contact failure where the second block pattern **350** is separated from the insulating layer structure **300** might be prevented.

[0046] The protective insulation layer **430** may be disposed in the peripheral region **20** on the buffer layer **115** and the shock absorbing structure **410**. The protective insulation layer **430** may at least partially overlap and cover the shock absorbing structure **410**. In exemplary embodiments of the present disclosure, the protective insulation layer **430** may completely cover the shock absorbing structure **410**.

[0047] For example, in a process for manufacturing the OLED device **100**, after the shock absorbing structure **410** is formed, metal particles generated in a process for etching a metal layer formed on the substrate **110** (e.g., a process for forming the source electrode **210**, the drain electrode **230**, the first power supply voltage wiring **380**, the second power supply voltage wiring **390**, the lower electrode **290**, the connection pattern **295**, etc.) may make their way into an opening formed inside the shock absorbing structure **410** (e.g., a space formed between two adjacent the first concave and convex patterns **411**). Here, when the protective insulation layer **430** is not formed on the shock absorbing structure **410**, the metal particles may generate a defect in a subsequent process (e.g., a process for forming the light emitting layer **330**). For example, the metal particles may escape from the opening formed inside the shock absorbing structure **410**, and then the light emitting layer **330** may be

formed with metal particles trapped therein. Thus, the metal particles may generate a defect of the light emitting layer **330**. In exemplary embodiments of the present disclosure, as the protective insulation layer **430** is disposed on the shock absorbing structure **410**, the OLED device **100** may prevent defects associated with the presence of the metal particles. For example, although metal particles generated in a process for forming the source electrode **210**, the drain electrode **230**, the first power supply voltage wiring **380**, the second power supply voltage wiring **390**, etc. is positioned in the opening formed inside the shock absorbing structure **410**, the metal particles may be prevented from escaping because the protective insulation layer **430** covers the shock absorbing structure **410**. In addition, as the protective insulation layer **430** covers the shock absorbing structure **410**, metal particles generated in a process for forming the lower electrode **290**, the connection pattern **295**, etc. may be blocked from entering an opening formed inside the shock absorbing structure **410**. Further, the protective insulation layer **430** together with the shock absorbing structure **410** may reduce an external impact generated in the outermost portion of the OLED device **100**.

[0048] In exemplary embodiments of the present disclosure, the protective insulation layer **430** may include organic materials. In addition, the planarization layer **270**, the first sub-block pattern **360**, and the protective insulation layer **430** may be simultaneously formed from substantially the same materials.

[0049] The lower electrode **290** may be disposed in the pixel region **30** on the planarization layer **270**. The lower electrode **290** may be in direct contact with the drain electrode **230** via the contact hole of the planarization layer **270**, and may be electrically connected to the semiconductor element **250**. The lower electrode **290** may include a metal, a metal alloy, metal nitride, conductive metal oxide, transparent conductive materials, etc. These may be used alone or in a suitable combination thereof. Alternatively, the lower electrode **290** may have a multi-layered structure including a plurality of layers.

[0050] The connection pattern **295** may be disposed on the planarization layer **270**, the first power supply voltage wiring **380**, and a portion of an upper surface of the first sub-block pattern **360**. For example, the connection pattern **295** may be spaced apart from the lower electrode **290** on the planarization layer **270**, and may extend in the first direction **D1**. The connection pattern **295** may be disposed in the display and peripheral regions **10** and **20**, which are located adjacent to a boundary the display region **10** and the peripheral region **20**, on the planarization layer **270**. The connection pattern **295** may be interposed between the first block pattern **345** and the first power supply voltage wiring **380** in the peripheral region **20**, and a portion of the connection pattern **295** may be interposed between the first sub-block pattern **360** and the second sub-block pattern **370**. Alternatively, the connection pattern **295** might not be disposed on an upper surface of the first sub-block pattern **360**.

[0051] The connection pattern **295** may electrically connect the first power supply voltage wiring **380** and the upper electrode **340**, and may receive the low power supply voltage from the first power supply voltage wiring **380**. In addition, the low power supply voltage may be applied to the upper electrode **340**. The connection pattern **295** may include a metal, an alloy of a metal, metal nitride, conduc-

tive metal oxide, transparent conductive materials, etc. These may be used alone or in a suitable combination thereof. Alternatively, the connection pattern 295 may have a multi-layered structure including a plurality of layers. In exemplary embodiments of the present disclosure, the lower electrode 290 and the connection pattern 295 may be simultaneously formed from substantially the same materials.

[0052] The pixel defining layer 310 may be disposed on a portion of the lower electrode 290, a portion of the connection pattern 295, and the planarization layer 270. The pixel defining layer 310 may at least partially cover both lateral portions of the lower electrode 290, and may have an opening exposing a portion of an upper surface of the lower electrode 290. The pixel defining layer 310 may include organic materials or inorganic materials. In exemplary embodiments of the present disclosure, the pixel defining layer 310 may include the organic materials.

[0053] The light emitting layer 330 may be disposed on the lower electrode 290 exposed by the opening of the pixel defining layer 310. The light emitting layer 330 may be formed from light emitting materials capable of generating different colors of light (e.g., red, blue, and green, etc.) according to sub-pixels. Alternatively, the light emitting layer 330 may generate white light by stacking a plurality of light emitting materials capable of generating different colors of light such as red, green, blue, etc. In this case, a color filter may be disposed on the light emitting layer 330 (e.g., on an upper surface of the TFE structure 450 to at least partially overlap the light emitting layer 330). The color filter may include a red color filter, a green color filter, and/or a blue color filter. Alternatively, the color filter may include a yellow color filter, a cyan color filter, and/or a magenta color filter. The color filter may include a photosensitive resin (or color photoresist), etc.

[0054] The first block pattern 345 may be disposed in the peripheral region 20 on the connection pattern 295. For example, the first block pattern 345 may be disposed on the connection pattern 295 under which the first power supply voltage wiring 380 is located. As illustrated in FIG. 1, the first block pattern 345 may surround the display region 10. In exemplary embodiments of the present disclosure, the first block pattern 345 may block a leakage of the second TFE layer 452. The first block pattern 345 may include inorganic materials or organic materials. In exemplary embodiments of the present disclosure, the first block pattern 345 may include the organic materials.

[0055] The second sub-block pattern 370 may be disposed on the first sub-block pattern 360 and a portion of the connection pattern 295. In exemplary embodiments of the present disclosure, the second sub-block pattern 370 together with the first sub-block pattern 360 may block a leakage of the second TFE layer 452. In addition, the second sub-block pattern 370 may include organic materials. In exemplary embodiments of the present disclosure, the pixel defining layer 310, the first block pattern 345, and the second sub-block pattern 370 may be simultaneously formed from substantially the same materials.

[0056] Accordingly, the second block pattern 350 including the first sub-block pattern 360 and the second sub-block pattern 370 may be fabricated. As illustrated in FIG. 1, the second block pattern 350 may be spaced apart from the first block pattern 345 in the first direction D1, and the second block pattern 350 may surround the first block pattern 345. The second block pattern 350 may at least partially overlap

the groove the insulating layer structure 300, and a height of the second block pattern 350 may be greater than a height of the first block pattern 345. In addition, the first block pattern 345 and the second block pattern 350 may be defined as the block structure 400.

[0057] The upper electrode 340 may be disposed on the pixel defining layer 310 and the light emitting layer 330. The upper electrode 340 may at least partially cover the light emitting layer 330 and the pixel defining layer 310, and may be disposed over the entire substrate 110. In exemplary embodiments of the present disclosure, the upper electrode 340 may at least partially cover the light emitting layer 330 and extend in the first direction D1, and may be electrically connected to the connection pattern 295 in the display region 10 that is located adjacent to a boundary of the display region 10 and the peripheral region 20. The upper electrode 340 may include a metal, a metal alloy, metal nitride, conductive metal oxide, transparent conductive materials, etc. These may be used alone or in a suitable combination thereof. Alternatively, the upper electrode 340 may have a multi-layered structure including a plurality of layers. Accordingly, the pixel structure 200 including the lower electrode 290, the light emitting layer 330, and the upper electrode 340 may be fabricated.

[0058] The first TFE layer 451 may be disposed on the upper electrode 340, the connection pattern 295, the block structure 400, the insulating interlayer 190, etc. The first TFE layer 451 may at least partially cover the upper electrode 340, the connection pattern 295, and the block structure 400, and may be disposed with a substantially uniform thickness along a profile of the upper electrode 340, the connection pattern 295, and the block structure 400. The first TFE layer 451 may block the permeation of moisture, water, oxygen, etc. which may deteriorate the pixel structure 200. In addition, the first TFE layer 451 may protect the pixel structure 200 from external impact. The first TFE layer 451 may include flexible inorganic materials.

[0059] The second TFE layer 452 may be disposed on the first TFE layer 451. The second TFE layer 452 may increase the flatness of the OLED device 100, and may protect the pixel structure 200. The second TFE layer 452 may include flexible organic materials.

[0060] The third TFE layer 453 may be disposed on the second TFE layer 452. The third TFE layer 453 may at least partially cover the second TFE layer 452, and may be disposed with a substantially uniform thickness along a profile of the second TFE layer 452. The third TFE layer 453 together with the first TFE layer 451 and the second TFE layer 452 may prevent the permeation of moisture, water, oxygen, etc. which may deteriorate the pixel structure 200. In addition, the third TFE layer 453 together with the first TFE layer 451 and the second TFE layer 452 may protect the pixel structure 200 from external impact. The third TFE layer 453 may include flexible inorganic materials. Accordingly, the TFE structure 450 including the first TFE layer 451, the second TFE layer 452, and the third TFE layer 453 may be fabricated.

[0061] Alternatively, the TFE structure 450 may have five layers structure where first through fifth TFE layers are stacked or seven layers structure where the first through seventh TFE layers are stacked.

[0062] As the OLED device 100 in accordance with exemplary embodiments of the present disclosure includes the insulating layer structure 300 having the groove (or the

insulating interlayer **195** having the opening **195**), a contact area of the second block pattern **350** may be relatively increased by the groove. Accordingly, although a width of the second block pattern **350** is relatively reduced, a contact failure where the second block pattern **350** is separated from the insulating layer structure **300** may be prevented.

[0063] FIGS. 3 through 8 are cross-sectional views illustrating a method of manufacturing an OLED device in accordance with exemplary embodiments of the present disclosure.

[0064] Referring to FIG. 3, a rigid glass substrate **105** may be provided. A substrate **110** including transparent materials or opaque materials may be formed on the rigid glass substrate **105**. The substrate **110** may be formed from a flexible transparent material such as a flexible transparent resin substrate. In exemplary embodiments of the present disclosure, the substrate **110** may have a structure in which a first organic layer, a first barrier film layer, a second organic layer, a second barrier film layer are sequentially stacked. The first and second barrier film layers may be formed from inorganic materials, and the first and second organic layers may be formed from organic materials. For example, each of the first and second barrier film layers may include silicon oxide, and may block water, moisture, etc. permeated through the first and second organic layers. Further, each of the first and second organic layers may include a polyimide-based resin.

[0065] Alternatively, the substrate **110** may be formed from a quartz substrate, a synthetic quartz substrate, a calcium fluoride substrate, a fluoride-doped quartz substrate, a sodalime glass substrate, a non-alkali glass substrate etc.

[0066] A buffer layer **115** may be formed on the substrate **110**. The buffer layer **115** may be formed over the entire substrate **110**. The buffer layer **115** may prevent the diffusion of metal atoms and/or impurities from the substrate **110**. In addition, the buffer layer **115** may control a rate of a heat transfer in a crystallization process for forming the active layer, thereby obtaining substantially uniform active layer. Further, the buffer layer **115** may increase a surface flatness of the substrate **110** when a surface of the substrate **110** is relatively irregular. According to a type of the substrate **110**, at least two buffer layers **115** may be disposed on the substrate **110**, or the buffer layer **115** may be omitted. For example, the buffer layer **115** may be formed from silicon compound, metal oxide, etc.

[0067] An active layer **130** may be formed in a pixel region **30** on the substrate **110**. The active layer **130** may be formed from an oxide semiconductor, an inorganic semiconductor (e.g., amorphous silicon, polysilicon, etc.), an organic semiconductor, etc.

[0068] A preliminary gate insulation layer **1150** may be formed on the buffer layer **115** and the active layer **130**. The preliminary gate insulation layer **1150** may at least partially cover the active layer **130** in a display region **10** on the buffer layer **115**, and may extend into a peripheral region **20** along a first direction D1. For example, the preliminary gate insulation layer **1150** may at least partially cover the active layer **130** on the buffer layer **115**, and may have a substantially flat upper surface without a step around the active layer **130**. Alternatively, the preliminary gate insulation layer **1150** may at least partially cover the active layer **130** on the buffer layer **115**, and may be disposed with a substantially uniform thickness along a profile of the active layer **130**. The preliminary gate insulation layer **1150** may be formed from

silicon compound, metal oxide, etc. For example, the preliminary gate insulation layer **1150** may include SiOx, SiNx, SiOxNy, SiOxCy, SiCxNy, AlOx, AlNx, TaOx, HfOx, ZrOx, TiOx, etc.

[0069] The gate electrode **170** may be formed in the pixel region **30** on the preliminary gate insulation layer **1150**. For example, the gate electrode **170** may be formed on a portion of the preliminary gate insulation layer **1150** under which the active layer **130** is located. The gate electrode **170** may be formed from a metal, a metal alloy, metal nitride, conductive metal oxide, transparent conductive materials, etc. For example, the gate electrode **170** may include Au, an alloy of Au, Ag, an alloy of Ag, Al, an alloy of Al, Pt, an alloy of Pt, Ni, Ti, Pd, Mg, Ca, Li, Cr, an alloy of Cr, Ta, W, Cu, an alloy of Cu, Mo, an alloy of Mo, Sc, Nd, Ir, AlNx, TiNx, CrNx, TaNx, WNx, SRO, ZnOx, SnOx, InOx, GaOx, ITO, IZO, etc. These may be used alone or in a suitable combination thereof. Alternatively, the gate electrode **170** may have a multi-layered structure including a plurality of layers.

[0070] A preliminary insulating interlayer **1190** may be formed on the preliminary gate insulation layer **1150** and the gate electrode **170**. The preliminary insulating interlayer **1190** may at least partially cover the gate electrode **170** in the display region **10** on the preliminary gate insulation layer **1150**, and may extend into the peripheral region **20** along the first direction D1. For example, the preliminary insulating interlayer **1190** may at least partially cover the gate electrode **170** on the preliminary gate insulation layer **1150**, and may have a substantially flat upper surface without a step around the gate electrode **170**. Alternatively, the preliminary insulating interlayer **1190** may at least partially cover the gate electrode **170** on the preliminary gate insulation layer **1150**, and may be formed with a substantially uniform thickness along a profile of the gate electrode **170**. The insulating interlayer **190** may include silicon compound, metal oxide, etc.

[0071] Referring to FIG. 4, an insulating layer structure **300**, including a gate insulation layer **150** and an insulating interlayer **190** and a shock absorbing structure **410** including first concave and convex patterns **411** and second concave and convex patterns **412**, may be formed by selectively etching the preliminary gate insulation layer **1150** and the preliminary insulating interlayer **1190**. For example, a first contact hole exposing a first side (e.g., a source region) of the active layer **130** and a second contact hole exposing a second side (e.g., a drain region) of the active layer **130** may be formed in the pixel region **30**, and an opening **195**, which exposes an upper surface of the gate insulation layer **150**, of the insulating interlayer **190** may be formed in the peripheral region **20**. The first concave and convex patterns **411** and the second concave and convex patterns **412** may be formed in the outermost portion of the peripheral region **20** on the buffer layer **115**.

[0072] The shock absorbing structure **410** may be spaced apart from the insulating layer structure **300** in the first direction D1, and the shock absorbing structure **410** and the insulating layer structure **300** may be located within the same layer. In addition, the first concave and convex patterns **411** may be formed on the buffer layer **115**, and may be spaced apart from each other. The second concave and convex patterns **412** may be formed on the first concave and convex patterns **411**, and may at least partially overlap the first concave and convex patterns **411**. Here, the first con-

cave and convex patterns **411** and the gate insulation layer **150** may be located within the same layer, and the second concave and convex patterns **412** and the insulating interlayer **190** may be located within the same layer. The shock absorbing structure **410** and the insulating layer structure **300** may be simultaneously formed from substantially the same materials.

[0073] A source electrode **210** and a drain electrode **230** may be formed in the pixel region **30** on the insulating interlayer **190**. The source electrode **210** may be in contact with a source region of the active layer **130** via a first contact hole formed by removing a first portion of the gate insulation layer **150** and the insulating interlayer **190**. The drain electrode **230** may be in contact with a drain region of the active layer **130** via a second contact hole formed by removing a second portion of the gate insulation layer **150** and the insulating interlayer **190**. Each of the source electrode **210** and the drain electrode **230** may be formed from a metal, an alloy, metal nitride, conductive metal oxide, transparent conductive materials, etc. These may be used alone or in a suitable combination thereof. Alternatively, each of the source electrode **210** and the drain electrode **230** may have a multi-layered structure including a plurality of layers. Accordingly, a semiconductor element **250** including the active layer **130**, the gate electrode **170**, the source electrode **210**, and the drain electrode **230** may be formed.

[0074] A first power supply voltage wiring **380** may be formed in the peripheral region **20** on the insulating layer structure **300**. In exemplary embodiments of the present disclosure, the first power supply voltage wiring **380** may be located adjacent to a boundary of the display region **10** and the peripheral region **20**, and may extend in a second direction D2 that is perpendicular to the first direction D1. In addition, the first power supply voltage wiring **380** might not overlap the opening **195** of the insulating interlayer **190**, and a low power supply voltage may be provided in the first power supply voltage wiring **380**. For example, the first power supply voltage wiring **380** may be formed from a metal, an alloy of a metal, metal nitride, conductive metal oxide, transparent conductive materials, etc. These may be used alone or in a suitable combination thereof. Alternatively, the first power supply voltage wiring **380** may have a multi-layered structure including a plurality of layers.

[0075] A second power supply voltage wiring **390** may be formed in the display region **10** on the insulating layer structure **300**. In exemplary embodiments of the present disclosure, the second power supply voltage wiring **390** may be located adjacent to a boundary of the display region **10** and the peripheral region **20**, and may be formed between the first power supply voltage wiring **380** and the drain electrode **230** on the insulating layer structure **300**. In addition, the second power supply voltage wiring **390** may extend in the second direction D2, and a high power supply voltage, which has a relatively high voltage level than the low power supply voltage, may be provided in the second power supply voltage wiring **390**. For example, the second power supply voltage wiring **390** may be formed from a metal, an alloy of a metal, metal nitride, conductive metal oxide, transparent conductive materials, etc. These may be used alone or in a suitable combination thereof. Alternatively, the second power supply voltage wiring **390** may have a multi-layered structure including a plurality of layers.

[0076] In exemplary embodiments of the present disclosure, the first power supply voltage wiring **380**, the second

power supply voltage wiring **390**, the source electrode **210**, and the drain electrode **230** may be located within the same layer, and may be simultaneously formed from substantially the same materials. For example, after a preliminary electrode layer is formed over the entire insulating layer structure **300**, the first power supply voltage wiring **380**, the second power supply voltage wiring **390**, the source electrode **210**, and the drain electrode **230** may be simultaneously formed by selectively etching the preliminary electrode layer.

[0077] A planarization layer **270** may be formed on the insulating layer structure **300**, the second power supply voltage wiring **390**, the source electrode **210**, and the drain electrode **230**, and might not overlap the first power supply voltage wiring **380**. The planarization layer **270** may be formed with a thickness sufficient to cover the second power supply voltage wiring **390** and the source and drain electrodes **210** and **230** on the insulating interlayer **190**. In this case, the planarization layer **270** may have a substantially flat upper surface, and a planarization process may be further performed on the planarization layer **270** to implement the flat upper surface of the planarization layer **270**. In addition, the planarization layer **270** may have a contact hole exposing an upper surface of the drain electrode **230**. The planarization layer **270** may include organic materials or inorganic materials. In exemplary embodiments of the present disclosure, the planarization layer **270** may be formed from organic materials.

[0078] A first sub-block pattern **360** may be formed in the peripheral region **20** on the insulating layer structure **300**. In exemplary embodiments of the present disclosure, the first sub-block pattern **360** may at least partially fill the opening **195** of the insulating interlayer **190**, and may be in direct contact with an upper surface of the gate insulation layer **150**. The first sub-block pattern **360** may at least partially overlap a portion of the first power supply voltage wiring **380**. In addition, the first sub-block pattern **360** and the planarization layer **270** may be located within the same layer. The first sub-block pattern **360** may include organic materials or inorganic materials. In exemplary embodiments of the present disclosure, the first sub-block pattern **360** may be formed from the organic materials such as polyimide, epoxy-based resin, acryl-based resin, polyester, photoresist, polyacryl-based resin, polyimide-based resin, a polyamide-based resin, a siloxane-based resin, etc.

[0079] A protective insulation layer **430** may be formed in the peripheral region **20** on the buffer layer **115** and the shock absorbing structure **410**. The protective insulation layer **430** may at least partially overlap and cover the shock absorbing structure **410**. In exemplary embodiments of the present disclosure, the protective insulation layer **430** may completely cover the shock absorbing structure **410**. The protective insulation layer **430** may be formed from organic materials, and the planarization layer **270**, the first sub-block pattern **360**, and the protective insulation layer **430** may be simultaneously formed from substantially the same materials. For example, after an organic layer is formed over the entire insulating layer structure **300**, the organic layer may be partially removed using a silt mask, a halftone mask, a halftone silt mask, etc., and then the planarization layer **270**, the first sub-block pattern **360**, and the protective insulation layer **430** may be simultaneously formed.

[0080] A lower electrode **290** may be formed in the pixel region **30** on the planarization layer **270**. The lower elec-

trode 290 may be in direct contact with the drain electrode 230 via the contact hole of the planarization layer 270, and may be electrically connected to the semiconductor element 250. The lower electrode 290 may be formed from a metal, a metal alloy, metal nitride, conductive metal oxide, transparent conductive materials, etc. These may be used alone or in a suitable combination thereof. Alternatively, the lower electrode 290 may have a multi-layered structure including a plurality of layers.

[0081] A connection pattern 295 may be formed on the planarization layer 270, the first power supply voltage wiring 380, and a portion of an upper surface of the first sub-block pattern 360. For example, the connection pattern 295 may be spaced apart from the lower electrode 290 on the planarization layer 270, and may extend in the first direction D1. The connection pattern 295 may be formed in the display and peripheral regions 10 and 20, which are located adjacent to a boundary the display region 10 and the peripheral region 20, on the planarization layer 270. The connection pattern 295 may be formed from a metal, an alloy of a metal, metal nitride, conductive metal oxide, transparent conductive materials, etc. These may be used alone or in a suitable combination thereof. Alternatively, the connection pattern 295 may have a multi-layered structure including a plurality of layers. In exemplary embodiments of the present disclosure, the lower electrode 290 and the connection pattern 295 may be simultaneously formed from substantially the same materials. For example, after a preliminary electrode layer is formed over the entire substrate 110, the lower electrode 290 and the connection pattern 295 may be simultaneously formed by selectively etching the preliminary electrode layer.

[0082] A pixel defining layer 310 may be formed on a portion of the lower electrode 290, a portion of the connection pattern 295, and the planarization layer 270. The pixel defining layer 310 may at least partially cover both lateral portions of the lower electrode 290, and may have an opening exposing a portion of an upper surface of the lower electrode 290. The pixel defining layer 310 may include organic materials or inorganic materials. In exemplary embodiments of the present disclosure, the pixel defining layer 310 may be formed from the organic materials.

[0083] A first block pattern 345 may be formed in the peripheral region 20 on the connection pattern 295. For example, the first block pattern 345 may be formed on the connection pattern 295 under which the first power supply voltage wiring 380 is located. As illustrated in FIG. 1, the first block pattern 345 may surround the display region 10. The first block pattern 345 may include inorganic materials or organic materials. In exemplary embodiments of the present disclosure, the first block pattern 345 may be formed from the organic materials.

[0084] A second sub-block pattern 370 may be formed on the first sub-block pattern 360 and a portion of the connection pattern 295. In addition, the second sub-block pattern 370 may be formed from organic materials. In exemplary embodiments of the present disclosure, the pixel defining layer 310, the first block pattern 345, and the second sub-block pattern 370 may be simultaneously formed from substantially the same materials. For example, after an organic layer is formed on the planarization layer 270, the connection pattern 295, and first sub-block pattern 360, the organic layer may be partially removed using the silt mask, the halftone mask, the halftone silt mask, etc., and then the

pixel defining layer 310, the first block pattern 345, and the second sub-block pattern 370 may be simultaneously formed.

[0085] Accordingly, the second block pattern 350 including the first sub-block pattern 360 and the second sub-block pattern 370 may be formed. As illustrated in FIG. 1, the second block pattern 350 may be spaced apart from the first block pattern 345 in the first direction D1, and the second block pattern 350 may surround the first block pattern 345. A height of the second block pattern 350 may be greater than a height of the first block pattern 345. In addition, the first block pattern 345 and the second block pattern 350 may be defined as the block structure 400.

[0086] A light emitting layer 330 may be formed on the lower electrode 290 exposed by the opening of the pixel defining layer 310. The light emitting layer 330 may be formed from light emitting materials capable of generating different colors of light (e.g., red, blue, and green, etc.) according to sub-pixels. Alternatively, the light emitting layer 330 may generate white light by stacking a plurality of light emitting materials capable of generating different colors such as red, green, blue, etc. In this case, a color filter may be formed on the light emitting layer 330. The color filter may include a red color filter, a green color filter, and/or a blue color filter. Alternatively, the color filter may include a yellow color filter, a cyan color filter, and/or a magenta color filter. The color filter may be formed from a photo-sensitive resin, etc.

[0087] An upper electrode 340 may be formed on the pixel defining layer 310 and the light emitting layer 330. The upper electrode 340 may at least partially cover the light emitting layer 330 and the pixel defining layer 310, and may be formed over the entire substrate 110. In exemplary embodiments of the present disclosure, the upper electrode 340 may at least partially cover the light emitting layer 330 and may extend in the first direction D1, and may be electrically connected to the connection pattern 295 in the display region 10 that is located adjacent to a boundary of the display region 10 and the peripheral region 20. The upper electrode 340 may be formed from a metal, a metal alloy, metal nitride, conductive metal oxide, transparent conductive materials, etc. These may be used alone or in a suitable combination thereof. Alternatively, the upper electrode 340 may have a multi-layered structure including a plurality of layers. Accordingly, a pixel structure 200 including the lower electrode 290, the light emitting layer 330, and the upper electrode 340 may be formed.

[0088] A first TFE layer 451 may be formed on the upper electrode 340, the connection pattern 295, the block structure 400, the insulating interlayer 190, etc. The first TFE layer 451 may at least partially cover the upper electrode 340, the connection pattern 295, and the block structure 400, and may be formed with a substantially uniform thickness along a profile of the upper electrode 340, the connection pattern 295, and the block structure 400. The first TFE layer 451 may prevent the permeation of moisture, water, oxygen, etc. that may deteriorate the pixel structure 200. In addition, the first TFE layer 451 may protect the pixel structure 200 from external impact. The first TFE layer 451 may be formed from flexible inorganic materials.

[0089] Referring to FIG. 8, a second TFE layer 452 may be formed on the first TFE layer 451. The second TFE layer 452 may increase the flatness of the OLED device 100, and

may protect the pixel structure 200. The second TFE layer 452 may be formed from flexible organic materials.

[0090] A third TFE layer 453 may be formed on the second TFE layer 452. The third TFE layer 453 may at least partially cover the second TFE layer 452, and may be formed with a substantially uniform thickness along a profile of the second TFE layer 452. The third TFE layer 453 together with the first TFE layer 451 and the second TFE layer 452 may prevent the pixel structure 200 from being deteriorated by the permeation of moisture, water, oxygen, etc. In addition, the third TFE layer 453 together with the first TFE layer 451 and the second TFE layer 452 may protect the pixel structure 200 from external impact. The third TFE layer 453 may be formed from flexible inorganic materials. Accordingly, a TFE structure 450 including the first TFE layer 451, the second TFE layer 452, and the third TFE layer 453 may be formed.

[0091] Alternatively, the TFE structure 450 may have five layers structure where first through fifth TFE layers are stacked or seven layers structure where the first through seventh TFE layers are stacked.

[0092] After the TFE structure 450 is formed, the rigid glass substrate 105 may be separated from the substrate 110. Accordingly, an OLED device 100 illustrated in FIG. 1 may be manufactured.

[0093] FIG. 9 is a cross-sectional view illustrating an OLED device in accordance with exemplary embodiments of the present disclosure, and FIG. 10 is a cross-sectional view illustrating an OLED device in accordance with exemplary embodiments of the present disclosure. An OLED device 500 illustrated in FIG. 9 may have a configuration substantially the same as or similar to that of an OLED device 100 described with reference to FIGS. 1 and 2 except for a shape of the first sub-block pattern 360. In reference to FIG. 9, omitted details may be understood to be at least similar to the details of corresponding elements described above with reference to FIGS. 1 and 2.

[0094] Referring to FIG. 9, an OLED device 500 may include a substrate 110, a buffer layer 115, a semiconductor element 250, an insulating layer structure 300, a shock absorbing structure 410, a first power supply voltage wiring 380, a second power supply voltage wiring 390, a planarization layer 270, a protective insulation layer 430, a block structure 400, a pixel structure 200, a connection pattern 295, a pixel defining layer 310, a TFE structure 450, etc. Here, the insulating layer structure 300 may include a gate insulation layer 150 and an insulating interlayer 190, and the block structure 400 may include a first block pattern 345 and a second block pattern 350. Here, the second block pattern 350 may include a first sub-block pattern 360 and a second sub-block pattern 370.

[0095] In exemplary embodiments of the present disclosure, the insulating layer structure 300 may have an opening 205 in the peripheral region 20. The opening 205 may at least partially overlap the first sub-block pattern 360. For example, the gate insulation layer 150 may have a first opening 155 exposing an upper surface of the buffer layer 115 in the peripheral region 20, and the insulating interlayer 190 may have a second opening 195 at least partially overlapping the first opening 155. Here, the first opening 155 and the second opening 195 may be defined as the opening 205 of the insulating layer structure 300.

[0096] The first sub-block pattern 360 may be disposed in the peripheral region 20 on the insulating layer structure

300. In exemplary embodiments of the present disclosure, the first sub-block pattern 360 may at least partially fill the opening 205 of the insulating layer structure 300, and may be in direct contact with an upper surface of the buffer layer 115. The first sub-block pattern 360 may at least partially overlap a portion of the first power supply voltage wiring 380. In addition, the first sub-block pattern 360 may block a leakage of the second TFE layer 452, and the first sub-block pattern 360 and the planarization layer 270 may be located within the same layer. The first sub-block pattern 360 may include organic materials or inorganic materials. In exemplary embodiments of the present disclosure, the first sub-block pattern 360 may include the organic materials.

[0097] In exemplary embodiments of the present disclosure, as the insulating layer structure 300 includes the opening 205 (e.g., the first opening 155 of the gate insulation layer 150 and the second opening 195 of the insulating interlayer 190), a contact area of the second block pattern 350 may be relatively increased by the opening 205. Accordingly, although a width of the second block pattern 350 is relatively reduced, a contact failure where the second block pattern 350 is separated from the insulating layer structure 300 may be prevented.

[0098] In some exemplary embodiments of the present disclosure, as illustrated in FIG. 10, the buffer layer 115 and the insulating layer structure 300 may have an opening 195, and the first sub-block pattern 360 may at least partially fill the opening 195. In this case, the first sub-block pattern 360 may be in direct contact with an upper surface of the substrate 110.

[0099] FIG. 11 is a cross-sectional view illustrating an OLED device in accordance with exemplary embodiments of the present disclosure. An OLED device 600 illustrated in FIG. 11 may have a configuration substantially the same as or similar to that of an OLED device 100 described with reference to FIGS. 1 and 2 except for a shape of the first sub-block pattern 360. In reference to FIG. 11, omitted details may be understood to be at least similar to the details of corresponding elements described above with reference to FIGS. 1 and 2.

[0100] Referring to FIG. 11, an OLED device 600 may include a substrate 110, a buffer layer 115, a semiconductor element 250, an insulating layer structure 300, a shock absorbing structure 410, a first power supply voltage wiring 380, a second power supply voltage wiring 390, a planarization layer 270, a protective insulation layer 430, a block structure 400, a pixel structure 200, a connection pattern 295, a pixel defining layer 310, a TFE structure 450, etc. Here, the insulating layer structure 300 may include a gate insulation layer 150 and an insulating interlayer 190, and the block structure 400 may include a first block pattern 345 and a second block pattern 350. Here, the second block pattern 350 may include a first sub-block pattern 360 and a second sub-block pattern 370.

[0101] In exemplary embodiments of the present disclosure, the insulating layer structure 300 may have a plurality of grooves 195 in the peripheral region 20. The grooves 195 may at least partially overlap the first sub-block pattern 360. For example, the insulating interlayer 190 may have a plurality of openings, and the openings may expose an upper surface of the gate insulation layer 150. Here, the plurality of openings may be defined as the grooves 195 of the insulating layer structure 300.

[0102] The first sub-block pattern 360 may be disposed in the peripheral region 20 on the insulating layer structure 300. In exemplary embodiments of the present disclosure, the first sub-block pattern 360 may at least partially fill the grooves 195 of the insulating layer structure 300, and may be in direct contact with an upper surface of the gate insulation layer 150. The first sub-block pattern 360 may at least partially overlap a portion of the first power supply voltage wiring 380. In addition, the first sub-block pattern 360 may block a leakage of the second TFE layer 452, and the first sub-block pattern 360 and the planarization layer 270 may be located within the same layer. The first sub-block pattern 360 may include organic materials or inorganic materials. In exemplary embodiments of the present disclosure, the first sub-block pattern 360 may include the organic materials.

[0103] The present invention may be applied to various display devices including an OLED device. For example, the present invention may be applied to vehicle-display device, a ship-display device, an aircraft-display device, portable communication devices, display devices for display or for information transfer, a medical-display device, etc.

[0104] Exemplary embodiments described herein are illustrative, and many variations can be introduced without departing from the spirit of the disclosure or from the scope of the appended claims. For example, elements and/or features of different exemplary embodiments may be combined with each other and/or substituted for each other within the scope of this disclosure and appended claims.

What is claimed is:

1. An organic light emitting display (OLED) device, comprising:

a substrate including a display region and a peripheral region at least partially surrounding the display region;
an insulating layer structure disposed on the substrate within both the display region and the peripheral region, the insulating layer structure including a groove in the peripheral region;

a plurality of pixel structures disposed in the display region on the insulating layer structure; and

a block structure disposed in the peripheral region and at least partially overlapping the groove of the insulating layer structure, the block structure at least partially filling the groove of the insulating layer structure.

2. The OLED device of claim 1, further comprising:

a shock absorbing structure disposed in the peripheral region on the substrate, the shock absorbing structure being spaced apart from the block structure in a first direction, the shock absorbing structure having a plurality of concave and convex patterns.

3. The OLED device of claim 2, wherein the shock absorbing structure is disposed at an edge of the substrate.

4. The OLED device of claim 3, wherein the shock absorbing structure and the insulating layer structure are located within a same layer, and are spaced apart from each other.

5. The OLED device of claim 2, further comprising:

a protective insulation layer at least partially overlapping the shock absorbing structure, the protective insulation layer at least partially covering the shock absorbing structure.

6. The OLED device of claim 2, further comprising:

a buffer layer disposed on the substrate,

wherein the insulating layer structure includes:

a gate insulation layer disposed on the buffer layer; and
an insulating interlayer disposed on the gate insulation layer.

7. The OLED device of claim 6, wherein the insulating interlayer has an opening exposing an upper surface of the gate insulation layer in the peripheral region, and wherein the groove of the insulating layer structure includes the opening.

8. The OLED device of claim 6, wherein the shock absorbing structure includes:

a plurality of stacked patterns, spaced apart from one another,

wherein each of the plurality of stacked patterns includes a convex pattern and a concave pattern in a stack.

9. The OLED device of claim 8, wherein the convex pattern of each of the plurality of stacked patterns are located within a same layer as either the gate insulating layer or the insulating interlayer and the concave pattern of each of the plurality of stacked patterns are located within a same layer as the other of the gate insulating layer or the insulating interlayer.

10. The OLED device of claim 1, further comprising:

a first power supply voltage wiring disposed in the peripheral region on the insulating layer structure, the first power supply voltage wiring being adjacent to a boundary where the display region and the peripheral region meet.

11. The OLED device of claim 10, wherein the block structure includes:

a first block pattern disposed on the first power supply voltage wiring; and

a second block pattern spaced apart from the first block pattern in a first direction, the second block pattern at least partially surrounding the first block pattern, and wherein the second block pattern at least partially overlaps the groove of the insulating layer structure.

12. The OLED device of claim 11, wherein a height of the second block pattern is greater than a height of the first block pattern.

13. The OLED device of claim 11, wherein the second block pattern includes:

a first sub-block pattern disposed on the insulating layer structure; and

a second sub-block pattern disposed on the first sub-block pattern.

14. The OLED device of claim 13, further comprising:

a connection pattern disposed in the display and peripheral regions, and interposed between the first block pattern and the first power supply voltage wiring in the peripheral region.

15. The OLED device of claim 14, wherein a portion of the connection pattern is interposed between the first sub-block pattern and the second sub-block pattern.

16. The OLED device of claim 14, wherein each of the plurality of pixel structures includes:

a lower electrode disposed on the substrate;

a light emitting layer disposed on the lower electrode; and

an upper electrode disposed on the light emitting layer, wherein the upper electrode is electrically connected to the connection pattern in the display region.

17. The OLED device of claim **16**, wherein the lower electrode and the connection pattern are located within a same layer.

18. An OLED device, comprising:

a substrate having a display region including a plurality of pixel regions and a peripheral region at least partially surrounding the display region;

an insulating layer structure disposed on the substrate, the insulating layer structure having an opening in the peripheral region;

a plurality of pixel structures disposed in the pixel regions on the insulating layer structure;

a block structure disposed in the peripheral region to at least partially overlap the opening of the insulating layer structure, the block structure at least partially filling the opening of the insulating layer structure; and

a shock absorbing structure disposed in the peripheral region on the substrate, the shock absorbing structure being spaced apart from the block structure, the shock absorbing structure having a plurality of concave and convex patterns.

19. The OLED device of claim **18**, further comprising:

a buffer layer disposed on the substrate,

wherein the insulating layer structure includes:

a gate insulation layer disposed on the buffer layer; and

an insulating interlayer disposed on the gate insulation layer,

wherein the gate insulation layer has a first opening exposing an upper surface of the buffer layer in the peripheral region, and the insulating interlayer has a second opening at least partially overlapping the first opening, and

wherein the opening of the insulating layer structure corresponds to the first and second openings.

20. An OLED device, comprising:

a substrate having a display region including a plurality of pixel regions and a peripheral region at least partially surrounding the display region;

an insulating layer structure disposed on the substrate, the insulating layer structure having a plurality of grooves disposed in the peripheral region;

a plurality of pixel structures disposed in the pixel regions on the insulating layer structure;

a block structure disposed in the peripheral region to at least partially overlap the grooves of the insulating layer structure, the block structure at least partially filling the grooves of the insulating layer structure; and

a shock absorbing structure disposed in the peripheral region on the substrate, the shock absorbing structure being spaced apart from the block structure, the shock absorbing structure having a plurality of concave and convex patterns.

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专利名称(译)	柔性有机发光显示装置		
公开(公告)号	US20190214587A1	公开(公告)日	2019-07-11
申请号	US16/244761	申请日	2019-01-10
[标]申请(专利权)人(译)	三星显示有限公司		
申请(专利权)人(译)	三星DISPLAY CO. , LTD.		
当前申请(专利权)人(译)	三星DISPLAY CO. , LTD.		
[标]发明人	KIM NAMJIN		
发明人	KIM, NAMJIN		
IPC分类号	H01L51/00 H01L51/52 H01L51/50 G09F9/30 H01L27/32		
CPC分类号	H01L51/0097 H01L51/5256 H01L51/5012 H01L51/5206 H01L51/5221 G09F9/301 H01L27/3246 H01L27/3276 H01L27/322 H01L51/5253 A63B21/154 A63B2210/50 H01L27/3258		
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摘要(译)

有机发光显示 (OLED) 器件包括具有显示区域和至少部分地围绕显示区域的外围区域的基板。绝缘层结构设置在显示区域和外围区域内的基板上。绝缘层结构包括外围区域中的凹槽。多个像素结构设置在绝缘层结构上的显示区域中。块结构设置在外围区域中，以便至少部分地与绝缘层结构的凹槽重叠。块结构至少部分地填充绝缘层结构的凹槽。

